

BAS28

**SURFACE MOUNT
DUAL, ISOLATED HIGH SPEED
SILICON SWITCHING DIODES**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAS28 consists of two electrically isolated ultra-high speed silicon switching diodes manufactured by the epitaxial planar process and packaged in an epoxy molded SOT-143 surface mount case. This device is designed for high speed switching applications.

MARKING CODE: A61 or JTW

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage	V _R	75	V
Peak Repetitive Reverse Voltage	V _{RRM}	85	V
Continuous Forward Current	I _F	250	mA
Peak Repetitive Forward Current	I _{FRM}	500	mA
Peak Forward Surge Current, tp=1.0µs	I _{FSM}	4.0	A
Peak Forward Surge Current, tp=1.0ms	I _{FSM}	2.0	A
Peak Forward Surge Current, tp=1.0s	I _{FSM}	1.0	A
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

SYMBOL

UNITS

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

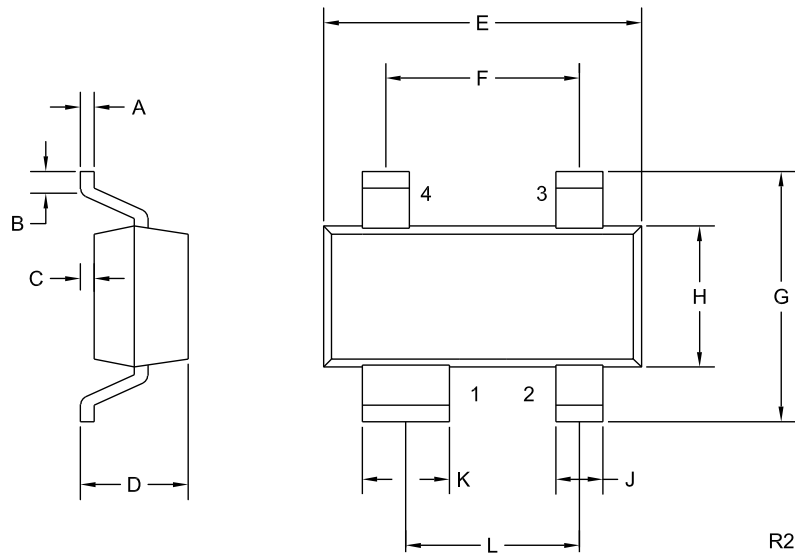
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =25V, T _A =150°C		30	µA
I _R	V _R =75V		1.0	µA
I _R	V _R =75V, T _A =150°C		50	µA
V _F	I _F =1.0mA		715	mV
V _F	I _F =10mA		855	mV
V _F	I _F =50mA		1.00	V
V _F	I _F =150mA		1.25	V
C _T	V _R =0, f=1.0MHz		2.0	pF
t _{rr}	I _F =I _R =10mA, I _{rr} =1.0mA, R _L =100Ω		6.0	ns
Q _s	I _F =10mA, V _R =5.0V, R _L =500Ω		45	pC
V _{FR}	I _F =10mA, t _r =20ns		1.75	V

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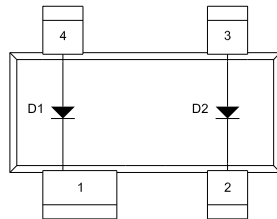
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SOT-143 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) CATHODE D1
- 2) CATHODE D2
- 3) ANODE D2
- 4) ANODE D1

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SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)

R7 (20-October 2010)